Prof. Ohmi's Paper

January－December, 1987

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3(C) Tadahiro Ohmi and Nobuo Mikoshiba, "Super Clean Room -Ultra Clean Technologies for Submicron LSI Fabrication," Extended Abstracts, 171st Electrochemical Society Spring Meeting, Philadelphia, Abstract No. 212, pp. 306-307, May 1987.

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4(C) Tadahiro Ohmi, Junich Murota, Y. Mitui, Kazuhiko Sugiyama, T. Kawasaki, and H. Kawano, "Ultra Clean Gas Supplying System for ULSI Fabrication and its Evaluation," Extended Abstracts, 171st Electrochemical Society Spring Meeting, Philadelphia, Abstract No. 216, pp. 312-313, May 1987.

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